



Substitute for Form 1449A/PTO
**INFORMATION DISCLOSURE
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Sheet 1 of 4

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Application Number	10/763136
Filing Date	January 22, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Nguyen, Tuan

Attorney Docket No: 303.588US3

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Group Art Unit	Unknown
Examiner Name	Nguyen, Tuan

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Attorney Docket No: 303.588US3

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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Application Number	Unknown
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Group Art Unit	Unknown
Examiner Name	Unknown

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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